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SEMICONDUCTOR

November 2013

## FQD7N20L N-Channel QFET<sup>®</sup> MOSFET 200 V, 5.5 A, 750 mΩ

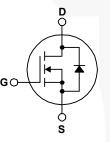
## Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

#### Features

- 5.5 A, 200 V,  $R_{DS(on)}$  = 750 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 2.75 A
- Low Gate Charge (Typ. 6.8 nC)
- Low Crss (Typ. 8.5 pF)
- RoHS Compliant
- · Low Level Gate Drive Requirement Allowing Direct Operating from Logic Drivers





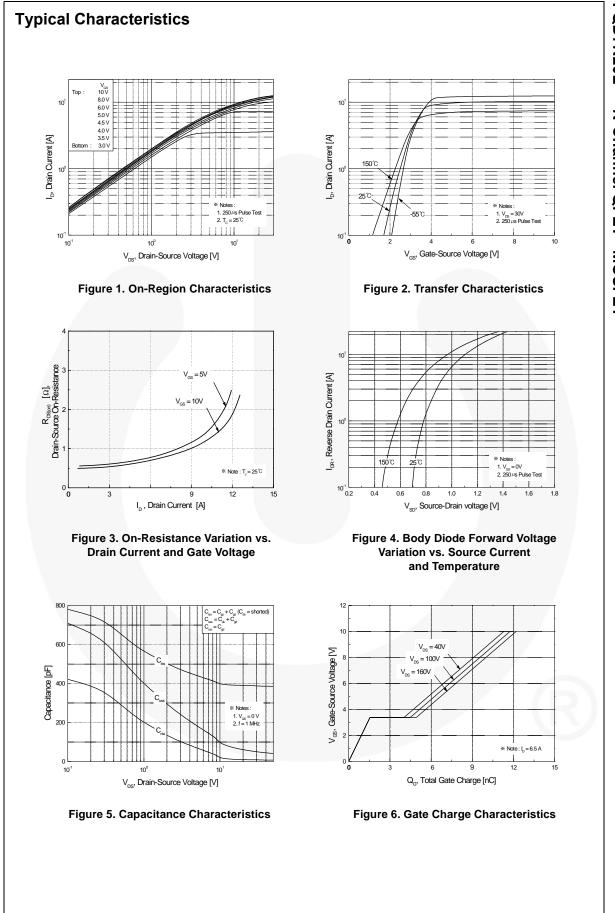
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

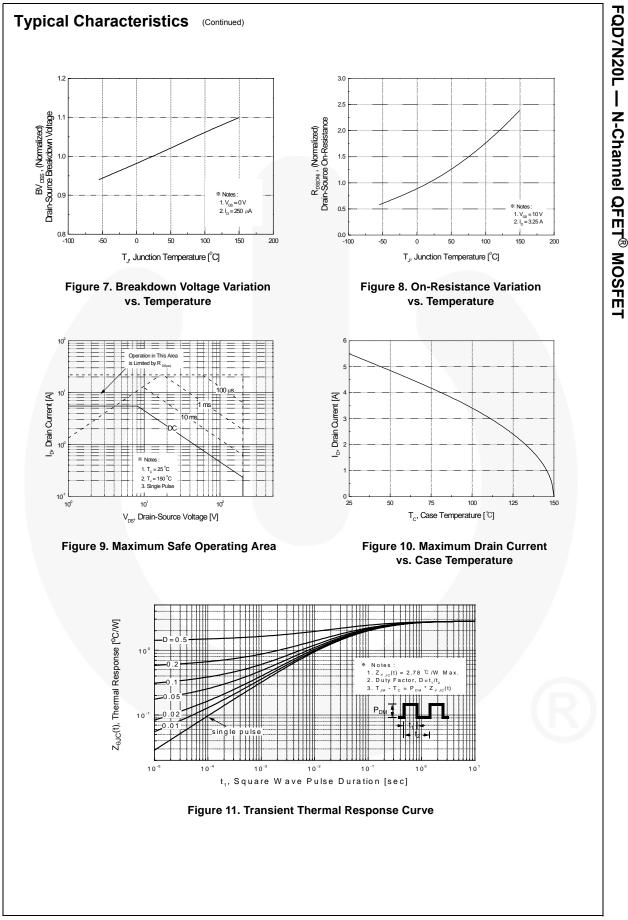
Symbol	Parameter	FQD7N20LTM	Unit
V <sub>DSS</sub>	Drain-Source Voltage	200	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )	5.5	А
	- Continuous (T <sub>C</sub> = 100°C)	3.48	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	22	A
V <sub>GSS</sub>	Gate-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	73	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	5.5	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *	2.5	W
	Power Dissipation (T <sub>C</sub> = 25°C)	45	W
	- Derate above 25°C	0.36	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	°C

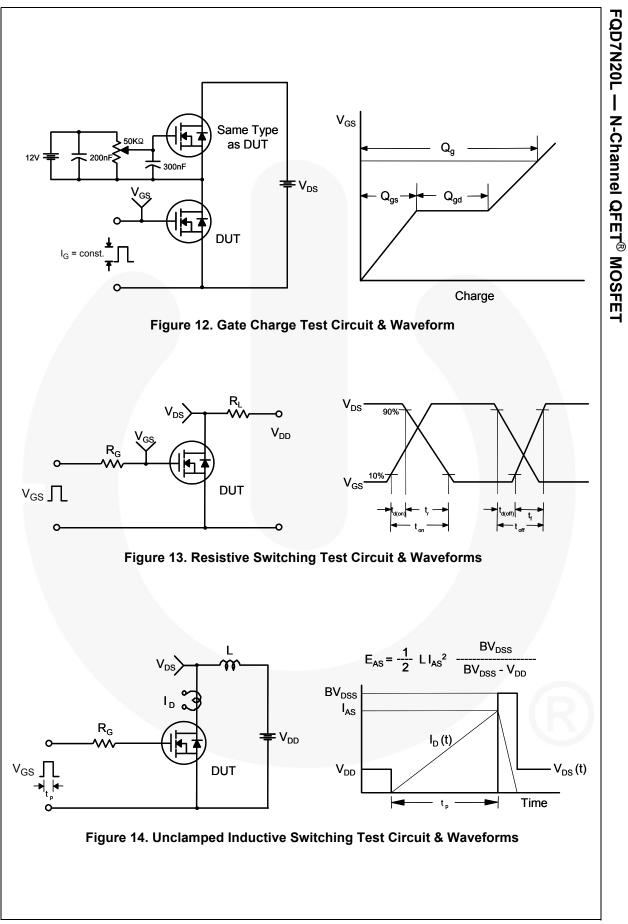
### **Thermal Characteristics**

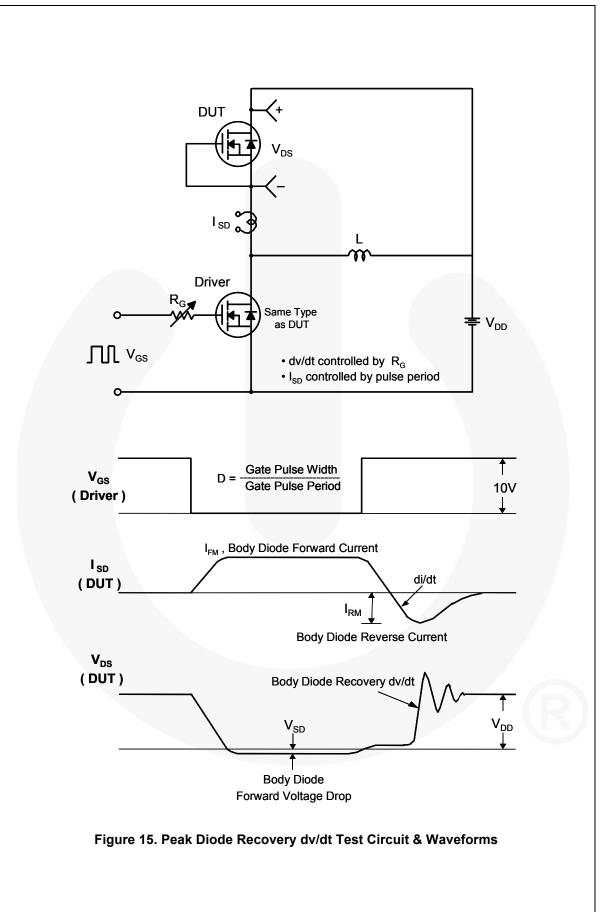
Symbol	Parameter	FQD7N20LTM	Unit	
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	2.78		
Р	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50		

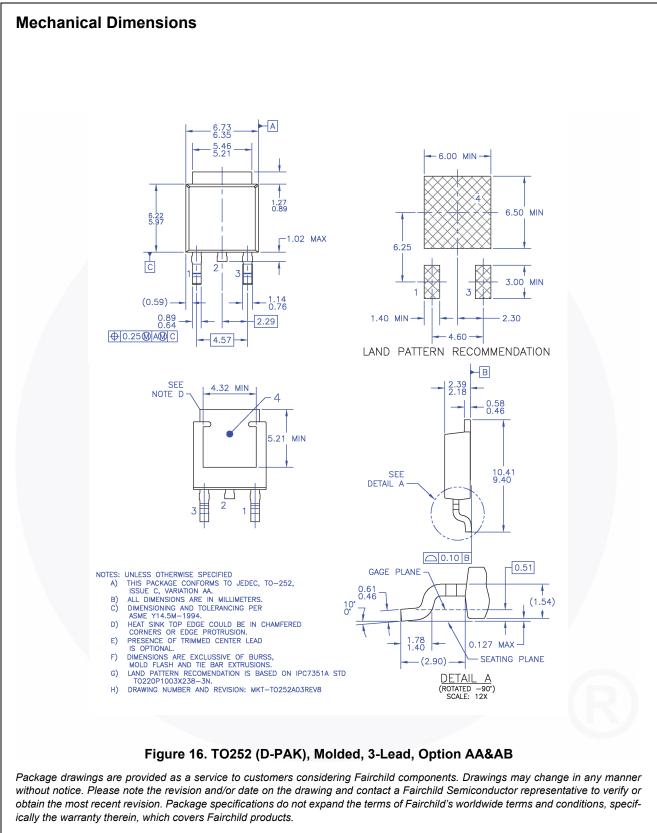
Part Number FQD7N20LTM		Top Mark	Pack	age	Packing Method Re		Size	Tape Width		Quantity 2500 units	
		FQD7N20L	DP	DPAK Tape a		eel 330 mm		16 mi	m 2		
ectri	cal Cha	racteristics	T <sub>C</sub> = 25°0	C unless ot	nerwise noted.						
Symbol		Parameter	-		Test Condition	s	Min.	Тур.	Max.	Unit	
Off Cha	aracterist	ics									
BV <sub>DSS</sub>	Drain-Sou	ain-Source Breakdown Voltage		V <sub>GS</sub> =	0 V, I <sub>D</sub> = 250 μA		200			V	
$\Delta BV_{DSS}$ / $\Delta T_J$	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$				0.17		V/°C		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V					1	μA		
			V <sub>DS</sub> = 160 V, T <sub>C</sub> = 125°C					10	μΑ		
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward		$V_{GS}$ = 20 V, $V_{DS}$ = 0 V					100	nA		
I <sub>GSSR</sub>	Gate-Bod	y Leakage Current,	Reverse	V <sub>GS</sub> =	-20 V, V <sub>DS</sub> = 0 V				-100	nA	
On Cha	aracterist	ics									
V <sub>GS(th)</sub>	Gate Thre	shold Voltage		-	V <sub>GS</sub> , I <sub>D</sub> = 250 μA		1.0		2.0	V	
R <sub>DS(on)</sub>	Static Drain-Source		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.75 \text{ A}$				0.59	0.75	Ω		
~	On-Resist		_		5 V, I <sub>D</sub> = 2.75 A 30 V, I <sub>D</sub> = 2.75 A			0.62	0.78	0	
9 <sub>FS</sub>	Forward	ransconductance	_	V <sub>DS</sub> =	$30 \text{ V}, \text{ I}_{\text{D}} = 2.75 \text{ A}$			5.6		S	
Dynam	ic Chara	cteristics									
C <sub>iss</sub>	Input Cap	acitance		V <sub>DS</sub> =	25 V, V <sub>GS</sub> = 0 V, MHz			390	500	pF	
C <sub>oss</sub>	Output Ca	apacitance		f = 1.0				55	70	pF	
C <sub>rss</sub>	Reverse 7	Fransfer Capacitance	e					8.5	11	pF	
Switch	ing Char	acteristics									
t <sub>d(on)</sub>		Delay Time	_	V -				12	35	ns	
t <sub>r</sub>	Turn-On F	Rise Time	_	$V_{DD} =$ $R_G = 2$	100 V, I <sub>D</sub> = 6.5 A,			125	260	ns	
t <sub>d(off)</sub>	Turn-Off	Delay Time	-	$r_G - 2$	10 12	(Note 4)		20	50	ns	
t <sub>f</sub>	Turn-Off F	all Time						65	140	ns	
Q <sub>g</sub>	Total Gate	e Charge		Vpe =	160 V, I <sub>D</sub> = 6.5 A,			6.8	9.0	nC	
Q <sub>gs</sub>	Gate-Sou	rce Charge		V <sub>GS</sub> =	-	(Note 4)		1.6		nC	
Q <sub>gd</sub>	Gate-Drai	n Charge						3.4		nC	
									1		
Drain-S		ode Characteri				S			5.5	A	
I <sub>SM</sub>		Pulsed Drain-Source							22	A	
V <sub>SD</sub>		Irce Diode Forward							1.5	V	
t <sub>rr</sub>		Recovery Time	, onage	$V_{GS} = 0 V, I_S = 5.5 A$ $V_{GS} = 0 V, I_S = 6.5 A,$			110		ns		
		Recovery Charge			$t = 100 \text{ A}/\mu \text{s}$			0.44		μC	
Q <sub>rr</sub>								0.11		μΟ	











Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT252-003

FQD7N20L — N-Channel QFET<sup>®</sup> MOSFET



No Identification Needed

Obsolete

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Not In Production

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Rev. 166

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